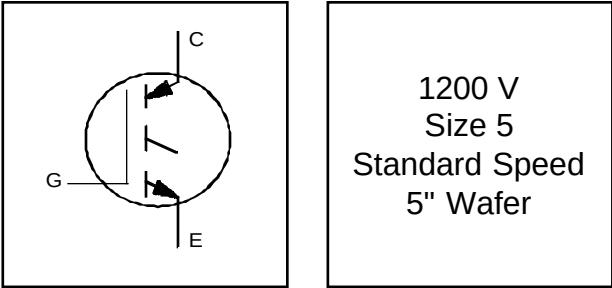


IRGCH50SE IGBT Die in Wafer Form



Electrical Characteristics (Wafer Form)

Parameter	Description	Guaranteed (Min/Max)	Test Conditions
$V_{CE(on)}$	Collector-to-Emitter Saturation Voltage	3.3V Max.	$I_C = 20A, T_J = 25^{\circ}C, V_{GE} = 15V$
$V_{(BR)CES}$	Collector-to-Emitter Breakdown Voltage	1200V Min.	$T_J = 25^{\circ}C, I_{CES} = 250\mu A, V_{GE} = 0V$
$V_{GE(th)}$	Gate Threshold Voltage	3.0V Min., 5.5V Max.	$V_{GE} = V_{CE}, T_J = 25^{\circ}C, I_C = 250\mu A$
I_{CES}	Zero Gate Voltage Collector Current	250 μA Max.	$T_J = 25^{\circ}C, V_{CE} = 1200V$
I_{GES}	Gate-to-Emitter Leakage Current	± 500 nA Max.	$T_J = 25^{\circ}C, V_{GE} = \pm 15V$

Mechanical Data

Normal Backmetal Composition, Thickness:	Cr-Ni-Ag (1kA-4kA-6kA)
Normal Front Metal Composition, Thickness:	99% Al, 1% Si (3 microns)
Dimensions:	0.257" x 0.260"
Wafer Diameter:	125mm, with std. < 100 > flat
Wafer thickness:	.015" + / -.003"
Relevant Die Mechanical Dwg. Number	01-5104
Minimum Street Width	100 Microns
Reject Ink Dot Size	0.25mm Diameter Minimum
Ink Dot Location	See Die Outline drawing below
Recommended Storage Environment:	Store in original container, in dessicated nitrogen, with no contamination

Reference Standard IR packaged part (for design) : IRGPH50S

Die Outline

